r

- High efficiency
- High current capability
- High Reliability
- High surge current capability
- Glass passivated chip junction
- Solder dip 275 °C max. 7 s, per JESD 22-B106

- : R-1

Molding [illegible] Ч

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| | | | | | |
|---|---|---|---|---|---|
| | FSM | A | 30 | | |
| Forward Surge Current (Non-repetitive)<br>@1ms, square wave, 1 cycle, Tj=25 | | | 60 | | |
| Current squared time<br>@1ms≤t8.3≤ms Tj=25 Rating of per diode | $I^2t$ | $A^2s$ | 3.735 | | |
| Typical junction capacitance<br>@Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C | Cj | pF | 15 | 13 | 8 |
| Storage Temperature | Tstg | | -55 ~ +150 | | |
| Junction Temperature | Tj | | -55 ~ +150 | | |

■ Ta=25 Unless otherwise specified

| | | | | | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|---|---|
| Maximum instantaneous forward voltage drop per diode | VF | V | IFM=1.0A | 1.0 | | | 1.3 | | 1.7 | | |
| Maximum DC reverse current at rated DC blocking voltage per diode | IR | μA | Tj=25 | | | | | | | | |

v7KHUPDO &KDUDFWHULVWLFV

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